描述 / Descriptions

SOT23-3 塑封封装 P 道 MOS 场效应管。P- CHANNEL MOSFET in a SOT23-3 Plastic Package.

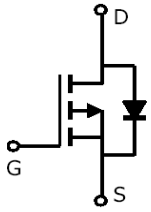
特征 / Features

V_{DS} (V) = -30V
I_D = -4.2 A (V_{GS} = -10V)
$R_{DS(ON)}$ < 60mΩ (V_{GS} = -10V)
$R_{DS(ON)}$ < 65mΩ (V_{GS} = -4.5V)
$R_{DS(ON)}$ < 120mΩ (V_{GS} = -2.5V)
符合 AEC-Q101 标准高可靠性要求，无卤产品。Qualified to AEC-Q101 Standards for High Reliability, HF Product.

用途 / Applications

适用于作负载开关或脉宽调制应用，满足汽车应用的严格要求。
This device is suitable for use as a load switch or in PWM applications, Meet the stringent requirements of automotive applications.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning

PIN1：G　　PIN 2：S　　PIN 3：D

印章代码 / Marking

Marking	QB1H

极限参数 / Absolute Maximum Ratings(Ta=25℃)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DS}	-30	V
Drain Current – Continuous	I_D	-4.2	A
Drain Current- Continuous [A]	I_D(T_a=70℃)	-3.5	A
Pulsed Drain Current [B]	I_{DM}	-30	A
Gate-Source Voltage	V_{GS}	±12	V
Total Power Dissipation [A]	P_D	1.4	W
Total Power Dissipation [A]	P_D(T_a=70℃)	1.0	W
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to 150	℃
Maximum Junction-to-Ambient [A]	$R_{\theta JA}$(T_a=70℃)	125	℃/W
Maximum Junction-to-Lead [C]	$R_{\theta JL}$	60	℃/W

电性能参数 / Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain–Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V V_{GS}=0V			-1	μA
		V_{DS}=-24V V_{GS}=0V T_J=55℃			-5	μA
Gate–Body Leakage.	I_{GSS}	V_{GS}=±12V V_{DS}=0V			±0.1	μA
On–State Drain Current	$I_{D(on)}$	V_{GS}=-4.5V V_{DS}=-5V	-25			A
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250μA	-0.7	-1	-1.3	V
Static Drain–Source On–Resistance	$R_{DS(on)(1)}$	V_{GS}=-10V I_D=-4.2A		52	60	mΩ
	$R_{DS(on)(2)}$	V_{GS}=-10V I_D=-4.2A T_J=125℃			75	
	$R_{DS(on)(3)}$	V_{GS}=-4.5V I_D=-4A		60	65	
	$R_{DS(on)(4)}$	V_{GS}=-2.5V I_D=-1A		75	120	
Forward Transconductance	g_{FS}	V_{DS}=-5V I_D=-5A	4	8		S
Drain–Source Diode Forward Voltage	V_{SD}	V_{GS}=0V I_S=-1A		-0.75	-1.0	V

电性能参数 / Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Input Capacitance	C_{iss}	V_{DS}=-15V V_{GS}=0V f=1MHz		957		pF
Output Capacitance	C_{oss}			115		
Reverse Transfer Capacitance	C_{rss}			77		
Gate resistance	R_g	V_{GS}=0V V_{DS}=0V, f=1MHz		6		Ω
Total Gate Charge	Q_g	V_{GS}=-4.5V V_{DS}=-15V I_D=-4A		9.4		nC
Gate Source Charge	Q_{gs}			2		
Gate Drain Charge	Q_{gd}			3		
Turn–On Delay Time	$t_{d(on)}$	V_{GS}=-10V R_L=3.6Ω V_{DS}=-15V R_{GEN}=6Ω		6.3		ns
Turn–On Rise Time	t_r			3.2		
Turn–Off Delay Time	$t_{d(off)}$			38.2		
Turn–Off Fall Time	t_f			12		
Body Diode Reverse Recovery Time	t_{rr}	I_F=-4A, dI/dt=100A/μs		20.2		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F=-4A, dI/dt=100A/μs		11.2		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

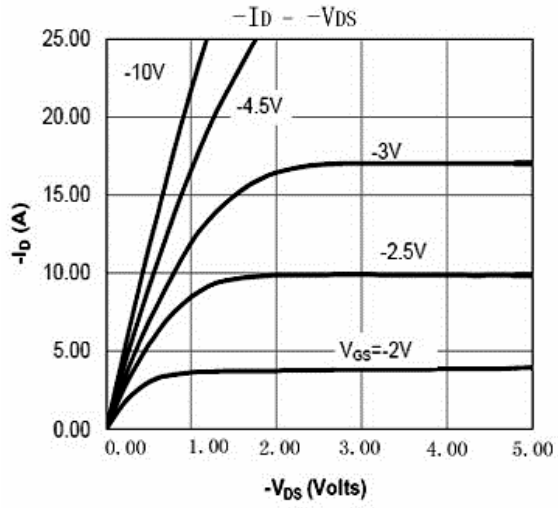
B: Repetitive rating, pulse width limited by junction temperature.

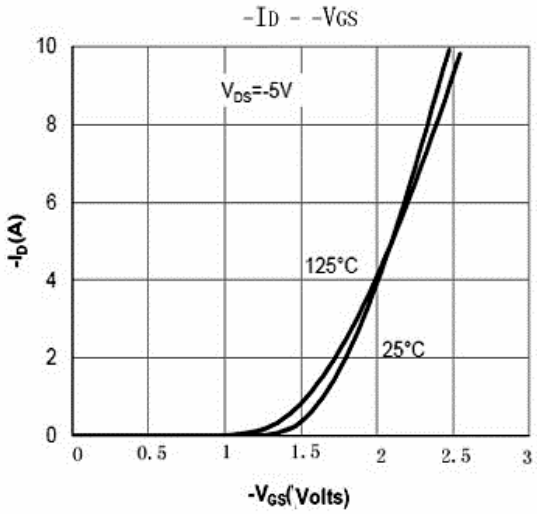
C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

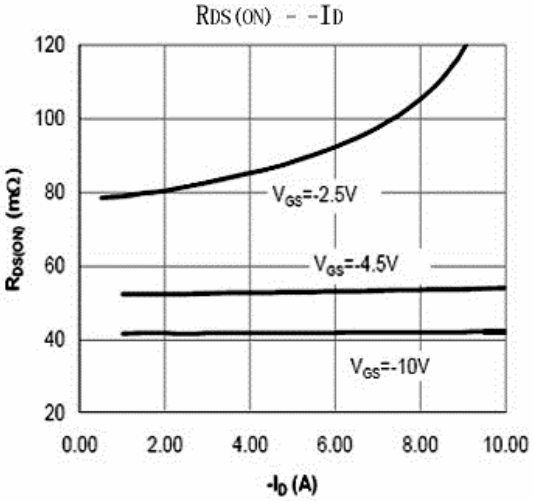
D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

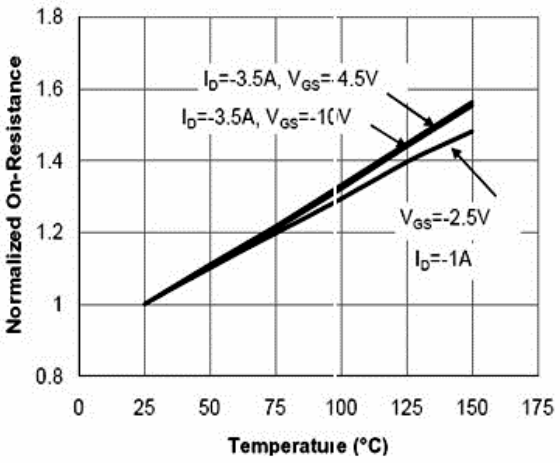
E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

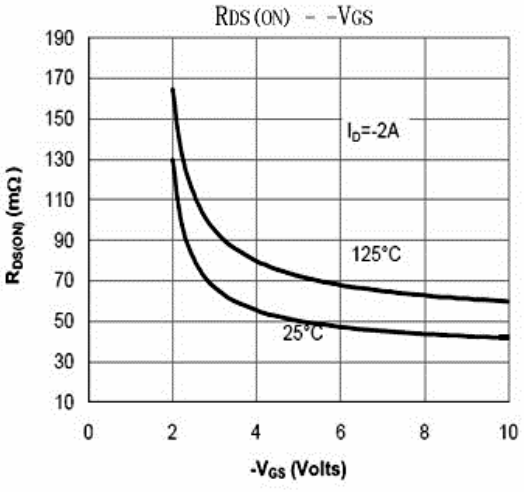
电参数曲线图 / Electrical Characteristic Curve

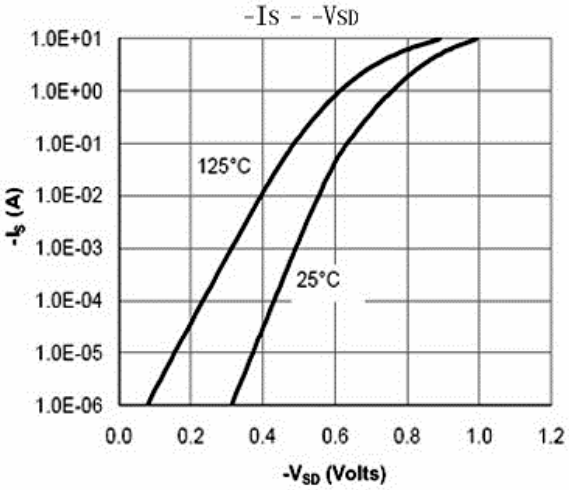




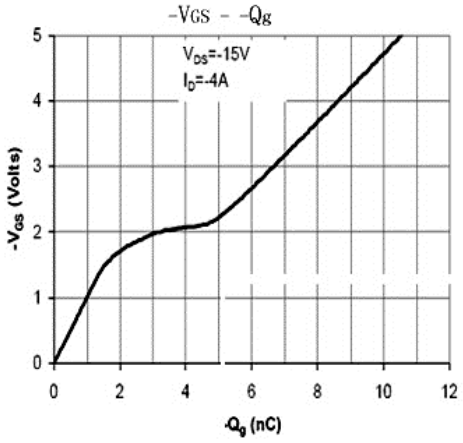


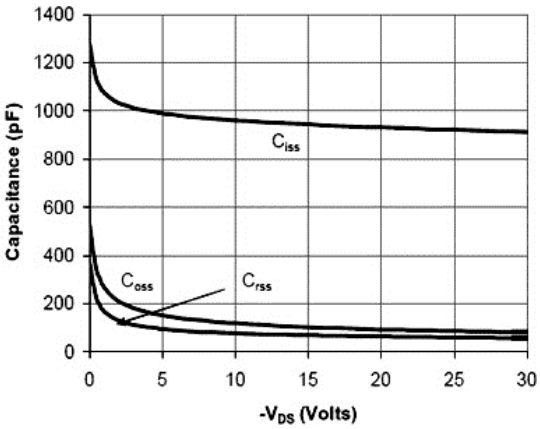


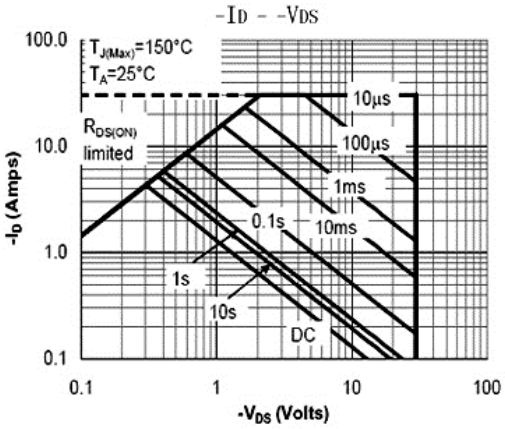




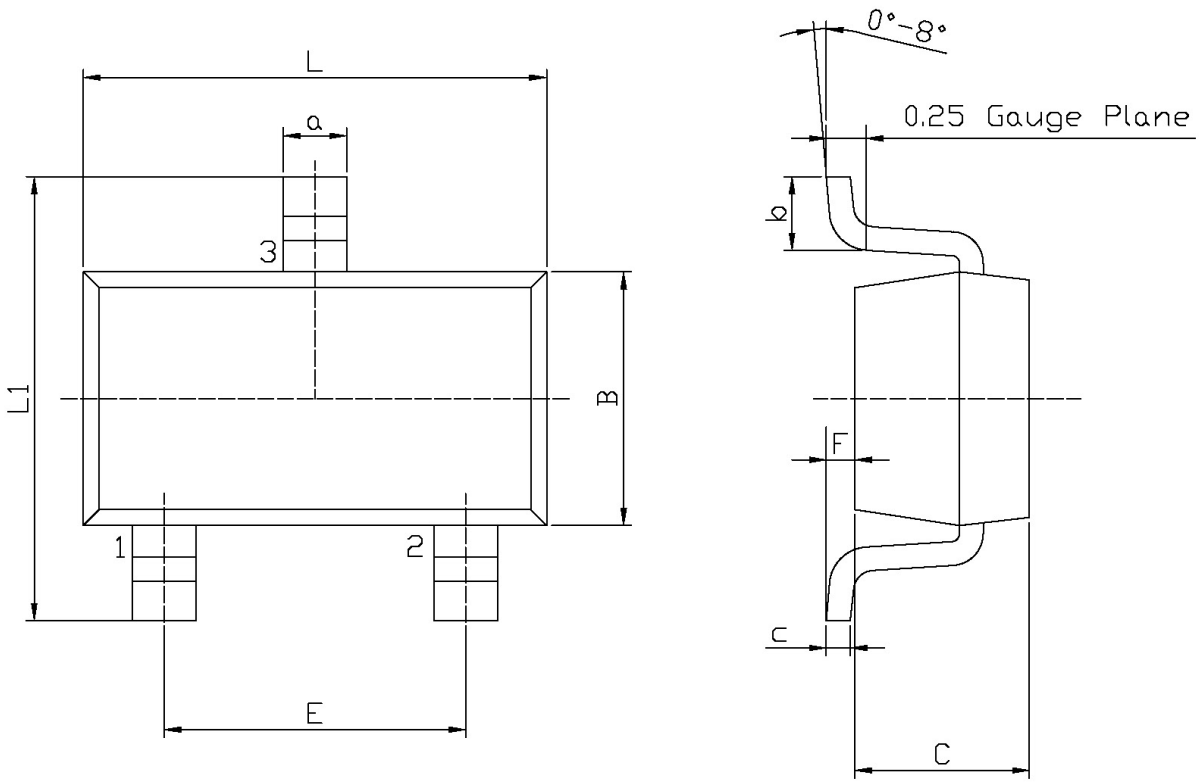
电参数曲线图 / Electrical Characteristic Curve







外形尺寸图 / Package Dimensions

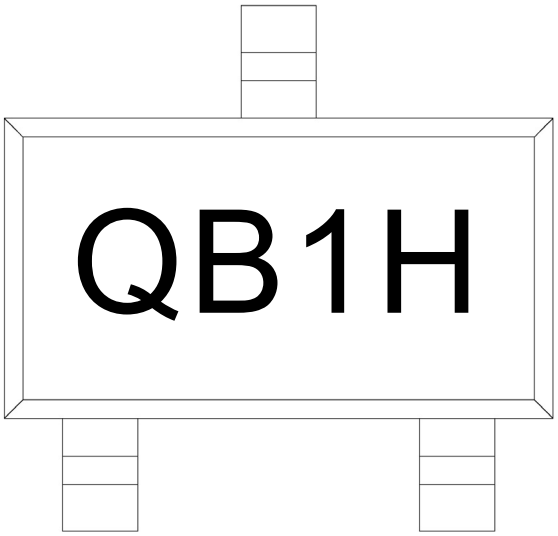


Unit: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.82	3.02	a	0.35	0.50
B	1.50	1.70	c	0.10	0.20
C	0.90	1.30	b	0.35	0.55
L1	2.60	3.00	F	0	0.15
E	1.80	2.00			

SOT23-3

印章说明 / Marking Instructions



说明：

Q： 为汽车无卤产品标识

B1： 为型号代码

H： 为公司代码

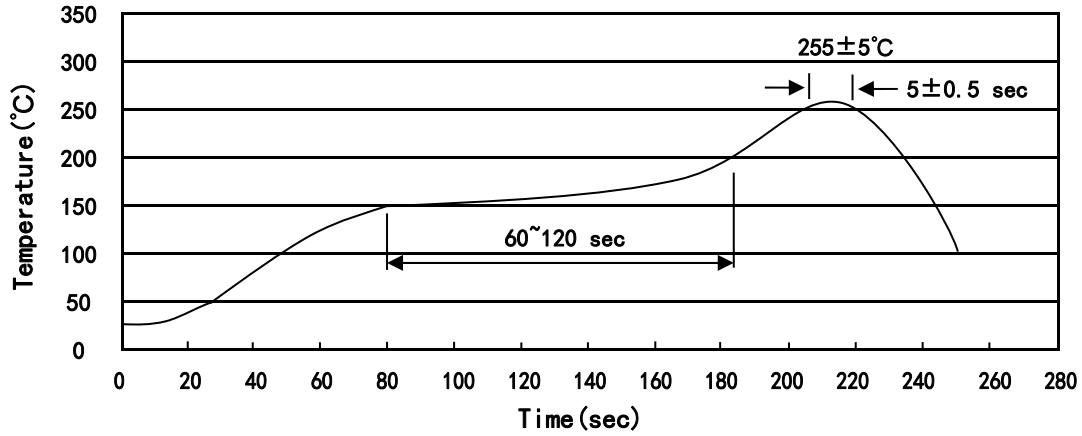
Note:

Q: Automobile halogen-free product Code

B1: Product Type Code

H: Company Code

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：	Note:
1、预热温度 150～200℃，时间 60～120sec;	1.Preheating:150~200℃, Time:60~120sec.
2、峰值温度 255±5℃，时间持续为 5±0.5sec;	2.Peak Temp.:255±5℃, Duration:5±0.5sec.
3、焊接制程冷却速度为 2～10℃/sec.	3. Cooling Speed: 2~10℃/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5℃ 时间：10±1 sec. Temp.:260±5℃ Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit：mm³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT23-3	3,000	10	30,000	4	120,000	7″ ×8	210×205×205	445×230×435

使用说明 / Notices